1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 2 A
- Reverse voltage: V_R ≤ 100 V
- Low forward voltage: V_F = 770 mV
- High power capability due to clip-bonding technology
- Extremely low leakage current I_R = 40 nA
- High temperature T_i ≤ 175 °C
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 160 °C; square wave	-	-	2	Α
V _R	reverse voltage	T _j = 25 °C	-	-	100	V
V _F	forward voltage	I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	770	830	mV
I _R	reverse current	$V_R = 100 \text{ V}; t_p \le 300 \mu\text{s}; \delta \le 0.02;$ $T_j = 25 ^{\circ}\text{C}$	-	40	150	nA





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	1 2	1 [[-] 2
2	А	anode	SOD123W	sym001

^[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG10020ELR	SOD123W	plastic surface mounted package; 2 leads	SOD123W			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG10020ELR	K8

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	100	V
I _F	forward current	T _{sp} = 155 °C; δ = 1		-	2.8	Α
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{amb} \le 80$ °C; square wave	[1]	-	2	Α
		δ = 0.5; f = 20 kHz; $T_{sp} \le$ 160 °C; square wave		-	2	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	680	mW
			[3]	-	1150	mW
			[1]	-	2140	mW
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

9. Thermal characteristics

Table 6. Thermal characteristics

	1						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	-	220	K/W
			[1][3]	-	-	130	K/W
			[1][4]	-	-	70	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[5]</u>	-	-	18	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.
- [5] Soldering point of cathode tab.

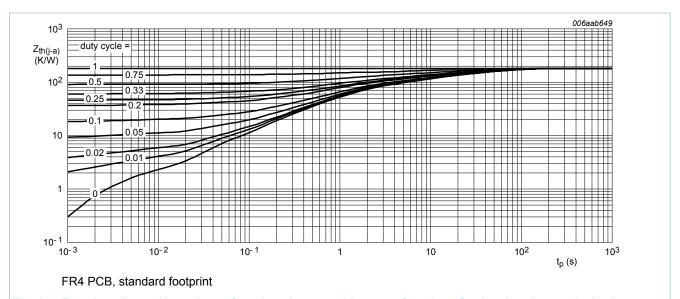


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

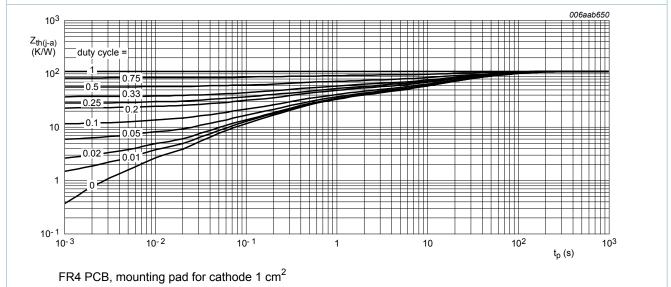
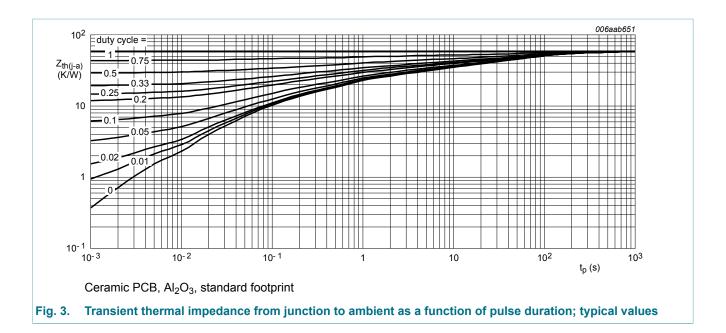


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



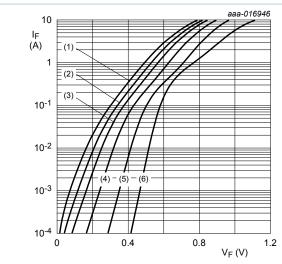
5 / 15

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	I_R = 1 mA; T_j = 25 °C; t_p = 300 µs; δ = 0.02	100	-	-	V
V _F	forward voltage	I_F = 0.1 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	505	565	mV
		I_F = 0.5 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	640	710	mV
		I_F = 0.7 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	675	740	mV
		I_F = 1 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	710	770	mV
		I_F = 1.6 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	750	810	mV
		I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	770	830	mV
		I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 125 °C	-	635	740	mV
I _R	reverse current	V_R = 10 V; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	4	-	nA
		$V_R = 60 \text{ V; } t_p \le 300 \mu\text{s; } \delta \le 0.02;$ $T_j = 25 ^{\circ}\text{C}$	-	12	-	nA
		V_R = 100 V; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	40	150	nA
		V_R = 100 V; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 125 °C	-	70	500	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	70	-	pF
		V _R = 4 V; f = 1 MHz; T _j = 25 °C	-	42	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	28	-	pF
rr	reverse recovery time	$I_F = 0.5 \text{ A}$; $I_R = 1 \text{ A}$; $I_{R(meas)} = 0.25 \text{ A}$; $I_j = 25 \text{ °C}$	-	3.7	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$	-	690	-	mV

6 / 15



(1)
$$T_i = 175 \, ^{\circ}C$$

(2)
$$T_i = 150 \, ^{\circ}C$$

(3)
$$T_i = 125 \, ^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_i = 25 \, ^{\circ}C$$

(6)
$$T_j = -40 \, ^{\circ}C$$

Fig. 4. Forward current as a function of forward voltage; typical values

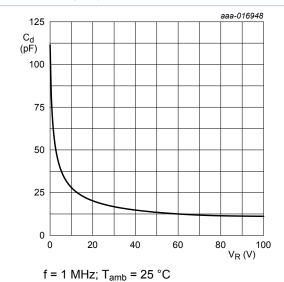
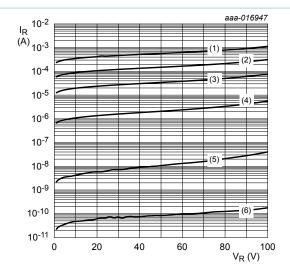


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



(1)
$$T_i = 175 \,^{\circ}C$$

(2)
$$T_j = 150 \, ^{\circ}\text{C}$$

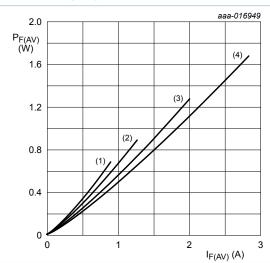
(3)
$$T_i = 125 \,^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_i = 25 \, ^{\circ}C$$

(6)
$$T_i = -40 \,^{\circ}\text{C}$$

Fig. 5. Reverse current as a function of reverse voltage; typical values



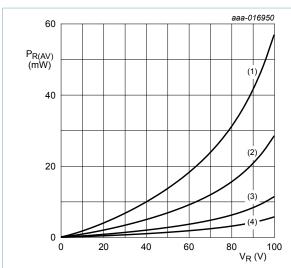
$$(1) \delta = 0.1$$

(2)
$$\delta = 0.2$$

$$(3) \delta = 0.5$$

$$(4) \delta = 1$$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T_i = 150 °C

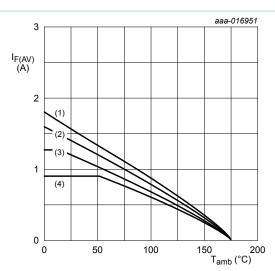
(1) $\delta = 1$ (DC)

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 175 °C

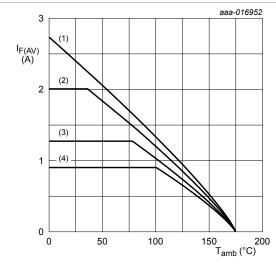
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

 T_i = 175 °C

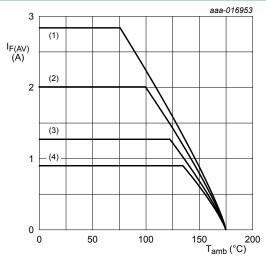
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 175 \,{}^{\circ}\text{C}$

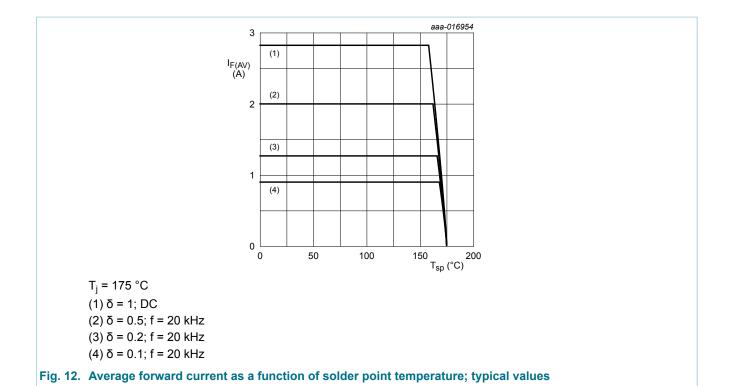
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

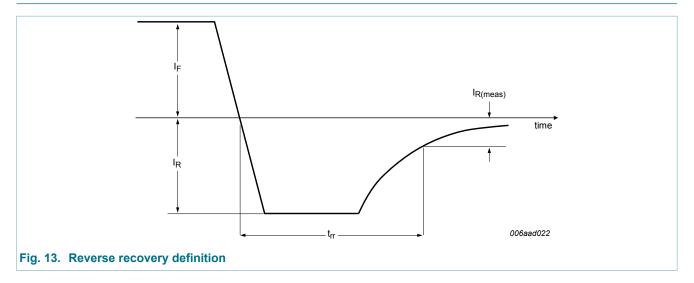
(3) δ = 0.2; f = 20 kHz

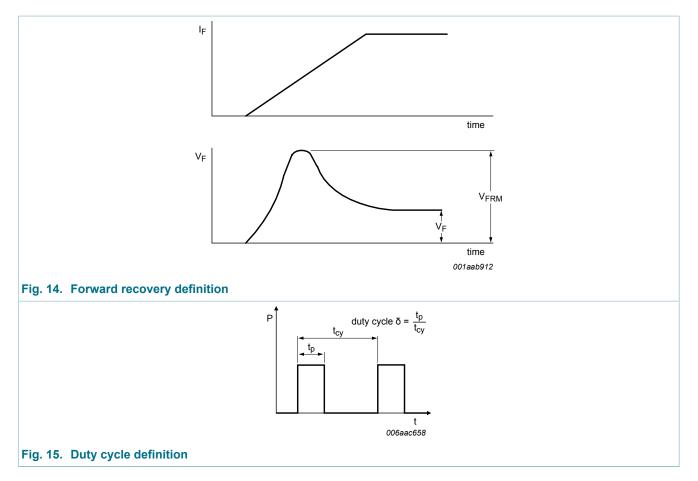
(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



11. Test information



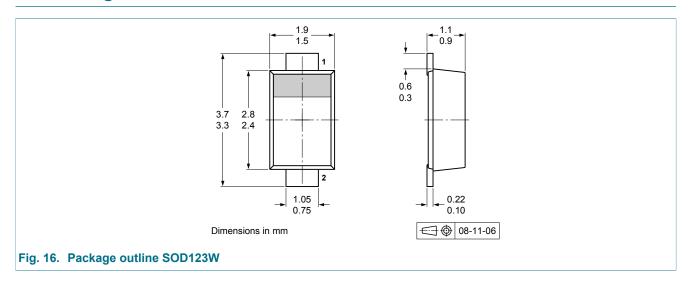


The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

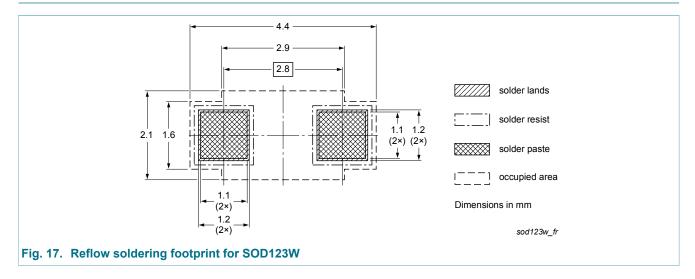
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG10020ELR v.2	20150507	Product data sheet	-	PMEG10020ELR v.1
Modifications:	Product status changed			
PMEG10020ELR v.1	20150219	Preliminary data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMEG10020ELR

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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	
6	Ordering information	
7	Marking	
8	Limiting values	
9	Thermal characteristics	
10	Characteristics	
11	Test information	
11.1	Quality information	
12	Package outline	
13	Soldering	
14	Revision history	
15	Legal information	
15.1	Data sheet status	
15.2	Definitions	
15.3	Disclaimers	
15.4	Trademarks	14

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